

isc Silicon NPN Power Transistor

2SC2073

DESCRIPTION

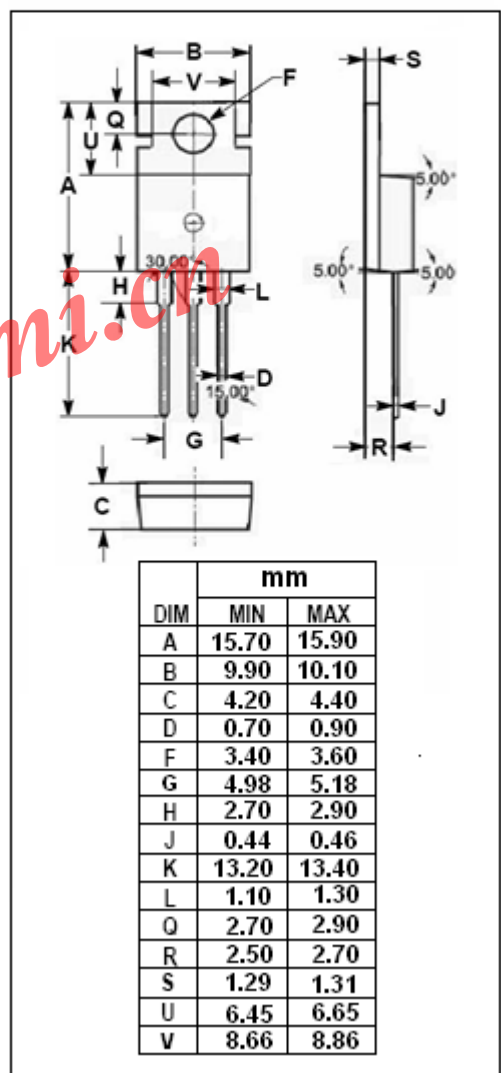
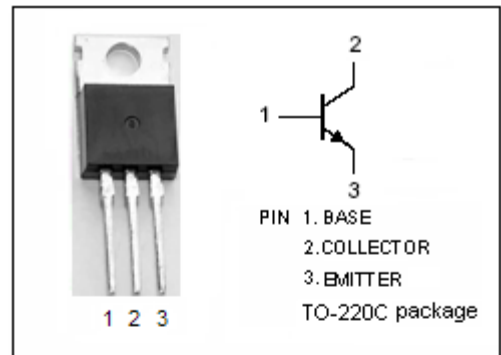
- Collector-Emitter Breakdown Voltage-
:V_{(BR)CEO}= 150V(Min)
- Wide Area of Safe Operation
- Complement to Type 2SA940

APPLICATIONS

- Power amplifier applications.
- Vertical output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	150	V
V _{CEO}	Collector-Emitter Voltage	150	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current-Continuous	1.5	A
I _B	Base Current-Continuous	0.5	A
P _C	Collector Power Dissipation @ T _a =25°C	1.5	W
	Collector Power Dissipation @ T _C =25°C	25	
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=500\text{mA}; I_B=50\text{mA}$			1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=500\text{mA}; V_{CE}=10\text{V}$			0.85	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=120\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	μA
h_{FE}	DC Current Gain	$I_C=500\text{mA}; V_{CE}=10\text{V}$	40		140	
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1\text{MHz}$		35		pF
f_T	Current-Gain—Bandwidth Product	$I_C=500\text{mA}; V_{CE}=10\text{V}$		4		MHz

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